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COAT
5 The first exposure regions and the second exposure regions of the photoresist layer are then removed for forming an array photoresist layer on the thin film layer. The array photoresist layer functions as a mask to perform an etching process to the thin film layer for forming an array thin film layer as a storage nodes in the DRAM.

In the claim:

1. (Once Amended) A method of forming storage nodes in a dynamic
10 random access memory (DRAM) on a semiconductor wafer, the semiconductor wafer comprising a substrate, a thin film layer positioned on the substrate, and a photoresist layer positioned on the thin film layer, the method comprising:
performing a first exposure process to form first exposure regions
15 including a plurality of lines that are parallel to each other and covering each storage node;

performing a second exposure process to form second exposure regions cutting the plurality of lines of the first exposure regions;

A2
20 performing a development process on the first exposure regions and the second exposure regions of the photoresist layer;

removing the first exposure regions and the second exposure regions of the photoresist layer to form an array photoresist layer on the thin film layer; and

25 using the array photoresist layer as a mask to perform an etching process to remove portions of the thin film layer not covered by the array photoresist layer so as to form an array thin film layer, the array thin film layer being used as the storage nodes in the DRAM.

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Cancel claims 3-6.